

## CLAIMS

1. A vapor phase growth apparatus comprising at least a sealable reactor, a wafer containing member installed within the reactor and having a wafer mounting portion on a surface thereof for holding a wafer, a gas supply member for supplying raw material gas towards the wafer, a heating member for heating the wafer, and a heat uniformizing member for holding the wafer containing member and uniformizing heat from the heating member, and

wherein raw material gas is supplied into the reactor in a high temperature environment while heating the wafer by using the heating member via the heat uniformizing member and the wafer containing member, to form a film grown on a surface of the wafer,

wherein a recess portion depressed in a dome shape is formed at a back side of the wafer containing member.

2. The vapor phase growth apparatus according to claim 1, wherein, when a height and a diameter of the recess portion provided in the wafer containing member are represented by H and D, respectively, a ratio of the height and the diameter  $H/D$  is between 0.01 and 2.10%.

3. The vapor phase growth apparatus according to claim 2, wherein the ratio of the height and the diameter

H/D is between 0.50 and 1.50%.

4. The vapor phase growth apparatus according to any one of claims 2 and 3, wherein the height H of the recess portion provided in the wafer containing member is between 0.02 and 3.00 mm.